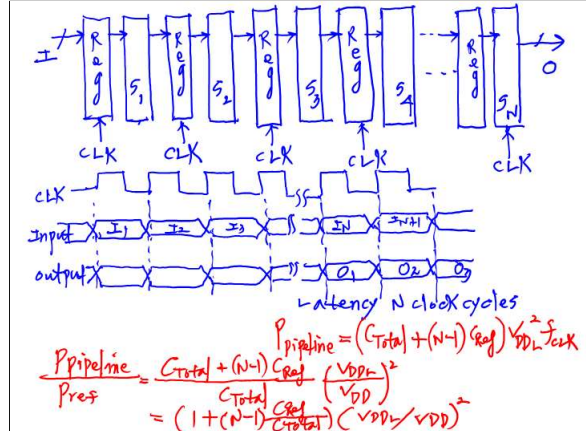
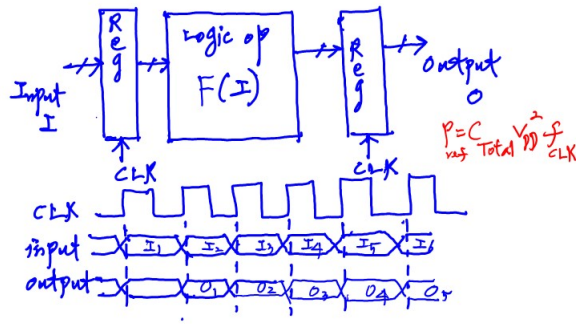


EE 222 W18 Lecture 12, Feb 22, 2018
 Reducing Power through Pipelining



Example

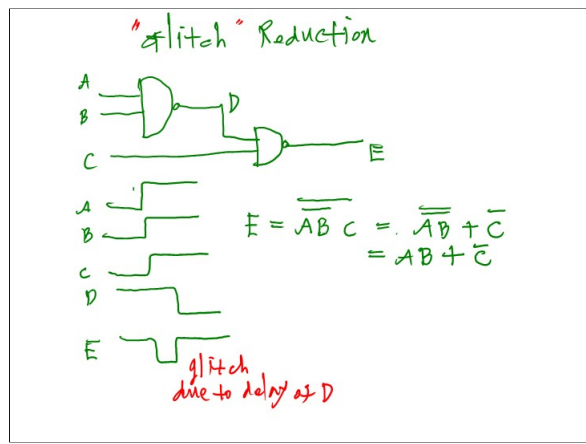
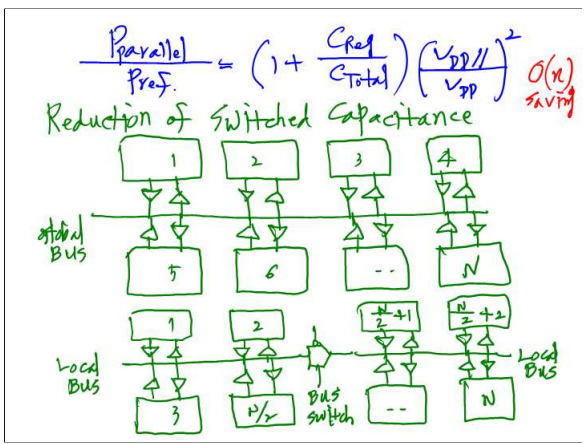
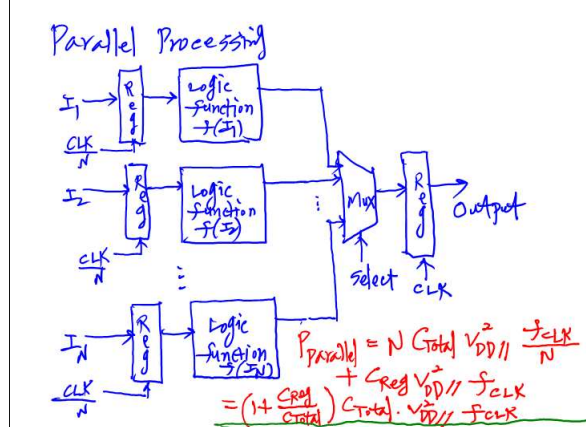
C_{Total}	C_{Reg}	V_{DD}	V_T	$V_{DD} // V_T$	f_{CLK}
	$\frac{C_{\text{Reg}}}{C_{\text{Total}}} = 0.1$	5V	0.8V	≈ 0.4	200MHz

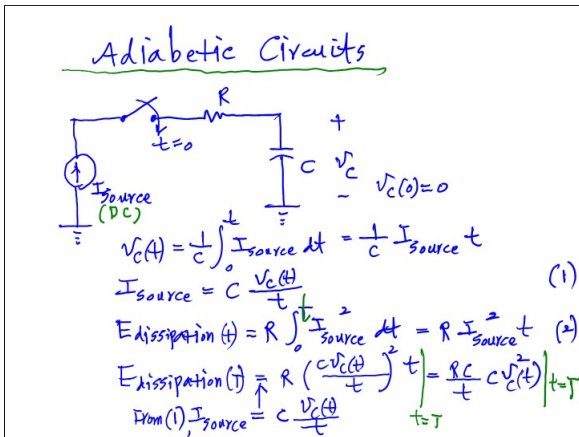
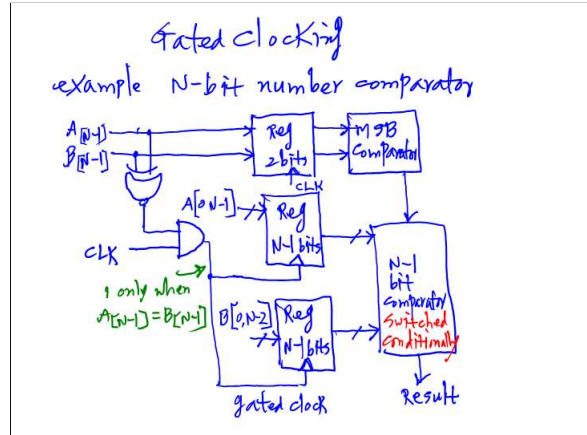
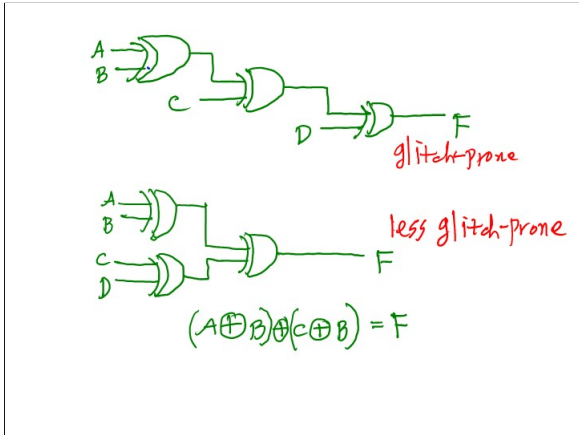
$\left(1 + (N-1) \frac{C_{\text{Reg}}}{C_{\text{Total}}}\right) \left(\frac{V_{DD} // V_T}{V_{DD}}\right)^2 = 1.0 \times (0.4)^2 = 0.16$

$\frac{C_{\text{Reg}}}{C_{\text{Total}}} \approx 0$ 84% saving

$N = 8$

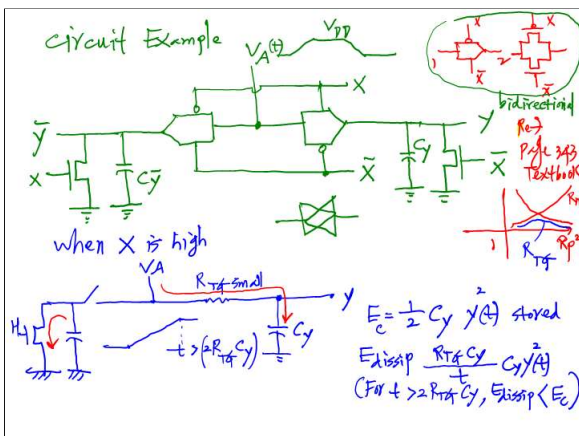
$\left[1 + 7(0.1)\right] (0.4)^2 = 1.7 \times 0.16 \approx 0.3$ 70% saving





Energy stored in the capacitor
 $E_C(t) = \frac{1}{2} C V_C^2(t)$
 Energy dissipated in R is
 $E_{dissip} = \frac{RC}{t} C V_C^2(t)$
 For $t > 2RC$ $E_{dissip} < E_C$

When the constant current source is used to 'slowly' charge up the capacitor, dissipated energy can be made smaller ($< E_C$). If the source current direction is reversed, then the energy stored in the capacitor less E_{dissip} can be returned!
The slower the time, the more can be returned.



Example NMOS PMOS
 $V_T = 0.53V$ $-0.51V$
 $k' = 98 \mu A/V^2$ $46 \mu A/V^2$
 $L = 10nm$ $10nm$
 $E_L = 0.4V$ $1.8V$

$I_{Dsat} = k' \frac{W}{L} [(1.2 - 0.53)^2]$ $I_{Dsp} = 46 \mu A/V^2 \cdot \frac{(1.2 - 0.51)^2}{2}$
 $\approx 98 \mu A/V^2 \cdot (0.4)^2$ $[V] = 0.11 mA$
 $\approx 0.22 mA$

$R_N = \frac{1.2V}{0.22mA} = 5.45 k\Omega$
 $R_P = \frac{1.2V}{0.11mA} = 10.9 k\Omega$
 $R_{Tf} = R_N || R_P = \frac{5.45 \times 10.9}{5.45 + 10.9} = 3.82 k\Omega$

$3.82 \times 10^{-15} \times 50 \times 10^{-15} = 191 \text{ pS}$
 $RC = 3.82 \times 10^{-15} \times 50 \times 10^{-15} = 191 \text{ pS}$
 If $t = 5RC$, then $t = 0.955 \text{ ns}$
 $t = 50RC$, $t = 50 \times 191 \text{ pS} = 9.55 \text{ ns}$
 $t = 1 \mu\text{s}$, $\frac{RC}{t} = \frac{191 \times 10^{-12}}{1 \times 10^{-6}} = 191 \times 10^{-6} \approx 0$

$C_y \frac{dy}{dt} = \frac{V_A - y}{R_{Tf}}$
 $(R_{Tf} C_y) \frac{dy}{dt} + y = V_A = \alpha t$, α is small (slowly rising V_A)
 $(R_{Tf} C_y s + 1) Y(s) = \frac{\alpha}{s^2}$
 $Y(s) = \frac{\alpha}{s^2 (R_{Tf} C_y s + 1)} = \frac{-R_{Tf} C_y \alpha}{s} + \frac{\alpha}{s^2} + \frac{(R_{Tf} C_y) \alpha}{R_{Tf} C_y s + 1}$
 $y(t) = -\alpha R_{Tf} C_y + \alpha t + \alpha (R_{Tf} C_y)^2 e^{-\frac{t}{R_{Tf} C_y}}$
 For large t , small α , small $R_{Tf} C_y$,
 $y(t) = \alpha t (= V_A) \Big|_{t=T}$ charge up to V_A level
 then the E_C energy can be retrieved to power supply side.
 Or the $y(t)$ can be used to drive other gates w/o V_A .

Next for X low,

Same analysis for $\bar{y}(t)$ with V_A supply (now using the energy retrieved)
 Thus, adiabatic logic with energy cycling.

Adiabatic AND2 gate

A	B	Vout	Vout
1	1	V_A	0
1	0	0	V_A
0	0	0	V_A
0	1	0	V_A

(C_{L1}, C_{L2} reset to 0)

Analysis of a CMOS Inverter with a Stepwise Power Supply.

$E_{step} = \frac{C (V_{DD}/2)^2}{2}$
 After n steps
 $E_C = n E_{step} = n \frac{1}{2} C \left(\frac{V_{DD}}{2}\right)^2 = \frac{1}{2n} C V_{DD}^2$

A More generalized analysis of adiabatic circuits

[Ref] R2 Ultra Low Power Bioelectronics
 by Rahul Saxena/Kar
 pp. 642-649

$V_{out}(s) = V_{in}(s) \frac{\frac{1}{Cs}}{R + \frac{1}{Cs}}$
 $= V_{in}(s) \frac{1}{1 + RCs}$, $I_R(s) = \frac{V_{in}(s) - V_{out}(s)}{R}$

when X is high then the best circuit model.

$$\Rightarrow I_R(s) = V_{in}(s) \frac{Cs}{1+RCs}$$

power dissipated in R

$$P_R(s) = |I_R(s)|^2 R$$

$$P_R(j\omega) = |I_R(j\omega)|^2 R$$

$$= |V_{in}(j\omega)|^2 \frac{j\omega C}{1+j\omega RC} \frac{j\omega C}{1+j\omega RC} R$$

$$= \frac{|V_{in}(j\omega)|^2}{R} \frac{\omega^2 (RC)^2}{1+\omega^2 (RC)^2}$$

Energy = $\int_0^T P_R(t) dt$, where $\omega T = 2\pi$ \uparrow $T = \frac{2\pi}{\omega}$

$$E_R(j\omega) = P_R(j\omega) T = \frac{|V_{in}(j\omega)|^2}{R} \frac{\omega^2 (RC)^2}{1+\omega^2 (RC)^2} \frac{2\pi}{\omega}$$

$$E_R(j\omega) = \frac{|V_{in}(j\omega)|^2}{R} \frac{\omega^2 (RC)^2}{1+\omega^2 (RC)^2} \frac{2\pi}{\omega}$$

$$E_C(j\omega) = \frac{1}{2} C |V_{out}(j\omega)|^2 \frac{2\pi}{\omega} \frac{1}{\omega} = \frac{1}{2} C |V_{in}(j\omega)|^2$$

when $V_o = V_{in}$

$$\frac{E_R(j\omega)}{E_C(j\omega)} = \frac{\frac{|V_{in}(j\omega)|^2}{R} \frac{\omega^2 (RC)^2}{1+\omega^2 (RC)^2} \frac{2\pi}{\omega}}{\frac{1}{2} C |V_{in}(j\omega)|^2}$$

$$= \frac{4\pi \omega^2 (RC)^2}{\omega RC (1+\omega^2 (RC)^2)}$$

$$= \frac{4\pi \omega RC}{1+(\omega RC)^2} \uparrow \frac{1}{\omega RC} = \frac{4\pi}{Q}$$

$$Q = \frac{1}{\omega RC} \text{ quality factor}$$

when $\omega RC < 1$

$Q = \frac{1}{\omega RC}$ is high when ωRC is small.
 ($\frac{E_R}{E_C}$ is made small)

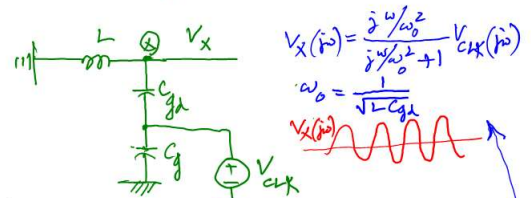
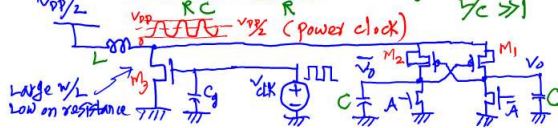
To make Q high, make $\omega RC = \frac{2\pi}{T} RC = 2\pi \frac{RC}{T}$ small by making $T \gg RC$.

Adiabatic clock

$$Q = \omega_0 RC \quad \omega_0 \text{ (resonance freq)} = \frac{1}{\sqrt{LC}}$$

$$= \frac{\sqrt{LC}}{RC} = \sqrt{\frac{L}{C}} \quad Q \text{ is high for small } R$$

$\frac{1}{C} \gg 1$



$$V_x(j\omega) = \frac{j\omega/\omega_0^2}{j\omega/\omega_0^2 + 1} V_{clk}(j\omega)$$

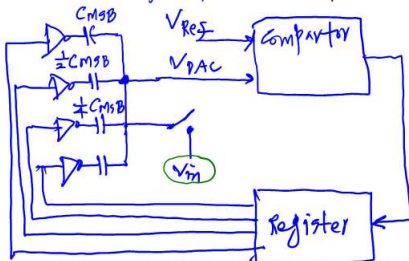
$$\omega_0 = \frac{1}{\sqrt{LC_{gd}}}$$

At ω_0 $\frac{V_x(s)}{Ls} = \frac{V_{clk}(s) - V_x(s)}{C_{gd}s} = 0$

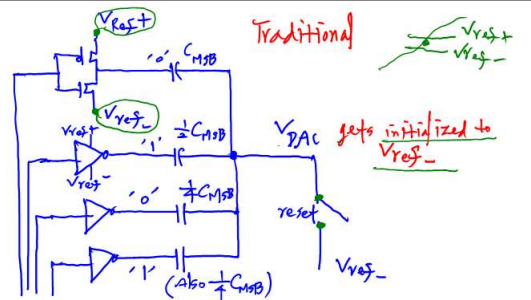
$$V_x(s) [C_{gd}s + \frac{1}{Ls}] = s V_{clk}(s) C_{gd}$$

$$V_x(s) = \frac{C_{gd}s}{C_{gd}s + \frac{1}{Ls}} V_{clk}(s) = \left[\frac{LC_{gd}s}{LC_{gd}s + 1} \right] V_{clk}(s)$$

Energy Efficient Comparator in ADC



Adiabatic charging for 3 MSBs only since for lower bits savings are $< 2X$.



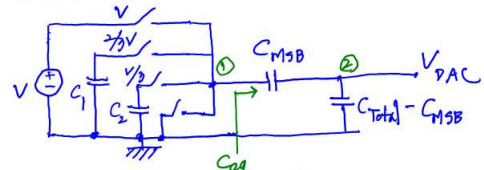
from register

Reset switch initializes V_{pac} to $V_{res-} \pm \sqrt{\frac{RT}{C_{total}}}$

$$C_{total} = 2C_{msb} + C_{parasitic}, T = \text{temperature} [K]$$

$$\begin{aligned}
 V_{DAC}(C_{Total}) &= C_{MSB} \cdot 0 + \frac{1}{2} C_{MSB} ('0' - '1') \\
 &\quad + \frac{1}{4} C_{MSB} \cdot 0 + \frac{1}{4} C_{MSB} ('0' - '1') \\
 &= C_{MSB} (1 + \frac{1}{4}) \cdot 0 + \frac{3}{4} C_{MSB} ('0' - '1') \\
 '0' - '1' &= V_{ref-} - V_{ref+} = -\Delta V \text{ (resolution)} \\
 \text{say } \Delta V &= \frac{1}{2} V \\
 V_{DAC} &= \frac{-\frac{3}{4} C_{MSB} (\frac{1}{2} V)}{C_{Total}} = -\frac{1}{4} \frac{C_{MSB}}{C_{MSB} + C_{par.}} V \\
 &\approx -\frac{1}{8} V
 \end{aligned}$$

Alternative scheme

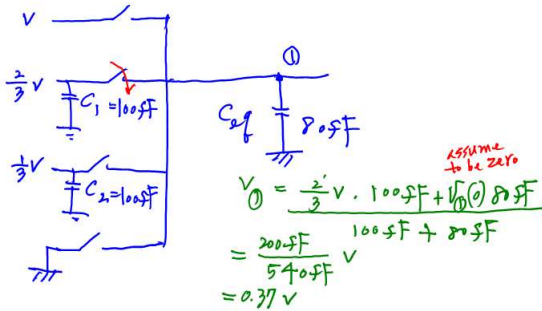


$$C_{eq} = \frac{C_{MSB} (C_{Total} - C_{MSB})}{C_{MSB} + (C_{Total} - C_{MSB})} = C_{MSB} \left(1 - \frac{C_{MSB}}{C_{Total}}\right)$$

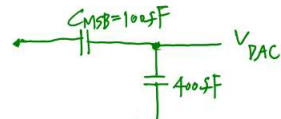
Switching energy is reduced by X3 (with n=3 levels of V used)

e.g.) $V = 1V$
 $C_{Total} = 500 fF$

if $C_{MSB} = 100 fF$
 $C_{eq} = 100 fF \left(1 - \frac{100 fF}{500 fF}\right) = 80 fF$



0.37 V



$$V_{DAC} = 0.37 V \cdot \frac{100}{100 + 400} = 0.074 V$$

